

TLP250

Transistor Inverter
 Inverter For Air Conditionor
 IGBT Gate Drive
 Power MOS FET Gate Drive

The TOSHIBA TLP250 consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP package.

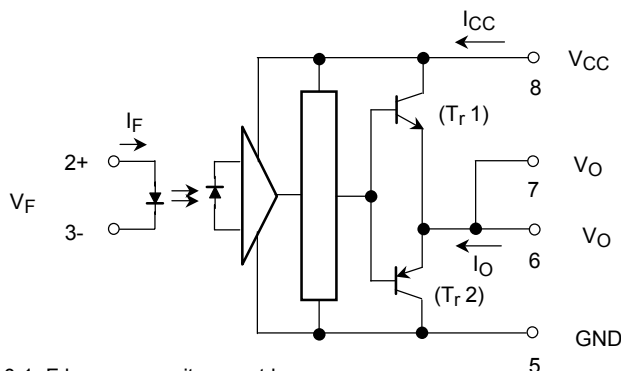
TLP250 is suitable for gate driving circuit of IGBT or power MOS FET.

- Input threshold current: $I_F=5\text{mA}(\text{max.})$
- Supply current (I_{CC}): $11\text{mA}(\text{max.})$
- Supply voltage (V_{CC}): $10\text{--}35\text{V}$
- Output current (I_O): $\pm 1.5\text{A}(\text{max.})$
- Switching time (t_{pLH}/t_{pHL}): $1.5\mu\text{s}(\text{max.})$
- Isolation voltage: $2500V_{\text{rms}}(\text{min.})$
- UL recognized: UL1577, file No.E67349
- Option (D4) type
 VDE approved: DIN VDE0884/06.92,certificate No.76823
 Maximum operating insulation voltage: 630VPK
 Highest permissible over voltage: 4000VPK

(Note) When a VDE0884 approved type is needed, please designate the "option (D4)"

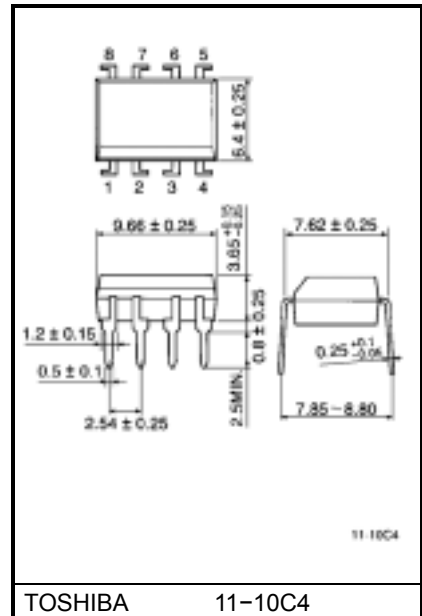
- Creepage distance: 6.4mm(min.)
 Clearance: 6.4mm(min.)

Schematic



A 0.1 μF bypass capacitor must be connected between pin 8 and 5 (See Note 5).

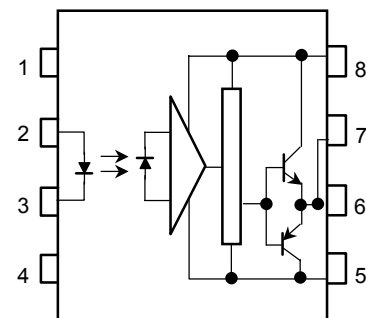
Unit in mm



TOSHIBA 11-10C4

Weight: 0.54 g

Pin Configuration (top view)



- 1 : N.C.
- 2 : Anode
- 3 : Cathode
- 4 : N.C.
- 5 : GND
- 6 : V_O (Output)
- 7 : V_O
- 8 : V_{CC}

Truth Table

| | | Tr1 | Tr2 |
|-----------|-----|-----|-----|
| Input LED | On | On | Off |
| | Off | Off | On |

Absolute Maximum Ratings (Ta = 25°C)

| Characteristic | | Symbol | Rating | Unit | |
|---|--|---------------------------|------------------------------|---------|--------|
| LED | Forward current | I_F | 20 | mA | |
| | Forward current derating (Ta ≥ 70°C) | $\Delta I_F / \Delta T_a$ | -0.36 | mA / °C | |
| | Peak transient forward current (Note 1) | I_{FPT} | 1 | A | |
| | Reverse voltage | V_R | 5 | V | |
| | Junction temperature | T_j | 125 | °C | |
| Detector | "H" peak output current ($P_W \leq 2.5\mu s, f \leq 15kHz$) (Note 2) | I_{OPH} | -1.5 | A | |
| | "L" peak output current ($P_W \leq 2.5\mu s, f \leq 15kHz$) (Note 2) | I_{OPL} | +1.5 | A | |
| | Output voltage | (Ta ≤ 70°C) | V_O | 35 | V |
| | | (Ta = 85°C) | | 24 | |
| | Supply voltage | (Ta ≤ 70°C) | V_{CC} | 35 | V |
| | | (Ta = 85°C) | | 24 | |
| | Output voltage derating (Ta ≥ 70°C) | | $\Delta V_O / \Delta T_a$ | -0.73 | V / °C |
| | Supply voltage derating (Ta ≥ 70°C) | | $\Delta V_{CC} / \Delta T_a$ | -0.73 | V / °C |
| Junction temperature | | T_j | 125 | °C | |
| Operating frequency (Note 3) | | f | 25 | kHz | |
| Operating temperature range | | T_{opr} | -20~85 | °C | |
| Storage temperature range | | T_{stg} | -55~125 | °C | |
| Lead soldering temperature (10 s) (Note 4) | | T_{sol} | 260 | °C | |
| Isolation voltage (AC, 1 min., R.H. ≤ 60%) (Note 5) | | BV_S | 2500 | Vrms | |

Note 1: Pulse width $P_W \leq 1\mu s$, 300pps

Note 2: Exponential waveform

Note 3: Exponential waveform, $I_{OPH} \leq -1.0A (\leq 2.5\mu s)$, $I_{OPL} \leq +1.0A (\leq 2.5\mu s)$

Note 4: It is 2 mm or more from a lead root.

Note 5: Device considered a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.

Note 6: A ceramic capacitor (0.1μF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1cm.

Recommended Operating Conditions

| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|----------------------------|-------------------|------|------|---------|------|
| Input current, on (Note 7) | $I_{F(ON)}$ | 7 | 8 | 10 | mA |
| Input voltage, off | $V_{F(OFF)}$ | 0 | — | 0.8 | V |
| Supply voltage | V_{CC} | 15 | — | 30 20 | V |
| Peak output current | I_{OPH}/I_{OPL} | — | — | ±0.5 | A |
| Operating temperature | T_{opr} | -20 | 25 | 70 85 | °C |

Note 7: Input signal rise time (fall time) < 0.5 μs.

Electrical Characteristics (Ta = -20~70°C, unless otherwise specified)

| Characteristic | | Symbol | Test Circuit | Test Condition | Min. | Typ.* | Max. | Unit | |
|--|--------------|---------------------------|--------------|--|--|-----------|-------|---------------|---|
| Input forward voltage | | V_F | — | $I_F = 10 \text{ mA}$, $T_a = 25^\circ\text{C}$ | | 1.6 | 1.8 | V | |
| Temperature coefficient of forward voltage | | $\Delta V_F / \Delta T_a$ | — | $I_F = 10 \text{ mA}$ | — | -2.0 | — | mV / °C | |
| Input reverse current | | I_R | — | $V_R = 5\text{V}$, $T_a = 25^\circ\text{C}$ | | — | 10 | μA | |
| Input capacitance | | C_T | — | $V = 0$, $f = 1\text{MHz}$, $T_a = 25^\circ\text{C}$ | — | 45 | 250 | pF | |
| Output current | "H" level | I_{OPH} | 3 | $V_{CC} = 30\text{V}$ (*1) | $I_F = 10 \text{ mA}$ $V_{8-6} = 4\text{V}$ | -0.5 | -1.5 | — | A |
| | "L" level | I_{OPL} | 2 | | $I_F = 0$ $V_{6-5} = 2.5\text{V}$ | 0.5 | 2 | — | |
| Output voltage | "H" level | V_{OH} | 4 | $V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $I_F = 5\text{mA}$ | 11 | 12.8 | — | V | |
| | "L" level | V_{OL} | 5 | $V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $V_F = 0.8\text{V}$ | — | -14.2 | -12.5 | | |
| Supply current | "H" level | I_{CCH} | — | $V_{CC} = 30\text{V}$, $I_F = 10\text{mA}$ $T_a = 25^\circ\text{C}$ | — | 7 | — | mA | |
| | | | | $V_{CC} = 30\text{V}$, $I_F = 10\text{mA}$ | — | — | 11 | | |
| | "L" level | I_{CCL} | — | $V_{CC} = 30\text{V}$, $I_F = 0\text{mA}$ $T_a = 25^\circ\text{C}$ | — | 7.5 | — | | |
| | | | | $V_{CC} = 30\text{V}$, $I_F = 0\text{mA}$ | — | — | 11 | | |
| Threshold input current | "Output L→H" | I_{FLH} | — | $V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $V_O > 0\text{V}$ | — | 1.2 | 5 | mA | |
| Threshold input voltage | "Output H→L" | I_{FHL} | — | $V_{CC1} = +15\text{V}$, $V_{EE1} = -15\text{V}$ $R_L = 200\Omega$, $V_O < 0\text{V}$ | 0.8 | — | — | V | |
| Supply voltage | | V_{CC} | — | | 10 | — | 35 | V | |
| Capacitance (input-output) | | C_S | — | $V_S = 0$, $f = 1\text{MHz}$ $T_a = 25$ | — | 1.0 | 2.0 | pF | |
| Resistance(input-output) | | R_S | — | $V_S = 500\text{V}$, $T_a = 25^\circ\text{C}$ $R.H. \leq 60\%$ | 1×10^{12} | 10^{14} | — | Ω | |

* All typical values are at $T_a = 25^\circ\text{C}$ (*1): Duration of I_O time $\leq 50\mu\text{s}$

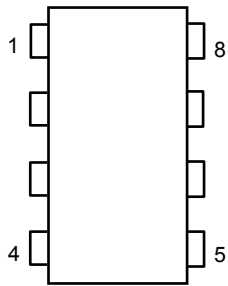
Switching Characteristics (Ta = -20~70°C , unless otherwise specified)

| Characteristic | Symbol | Test Circuit | Test Condition | Min. | Typ.* | Max. | Unit |
|---|-----------------|------------------|--|-------|-------|------|--------|
| Propagation delay time | L→H | t _{pLH} | I _F = 8mA (Note 7) V _{CC1} = +15V, V _{EE1} = -15V R _L = 200Ω | — | 0.15 | 0.5 | μs |
| | H→L | t _{pHL} | | — | 0.15 | 0.5 | |
| Output rise time | t _r | 6 | | — | — | — | |
| Output fall time | t _f | | | — | — | — | |
| Common mode transient immunity at high level output | C _{MH} | 7 | V _{CM} = 600V, I _F = 8mA V _{CC} = 30V, Ta = 25°C | -5000 | — | — | V / μs |
| Common mode transient immunity at low level output | C _{ML} | 7 | V _{CM} = 600V, I _F = 0mA V _{CC} = 30V, Ta = 25°C | 5000 | — | — | V / μs |

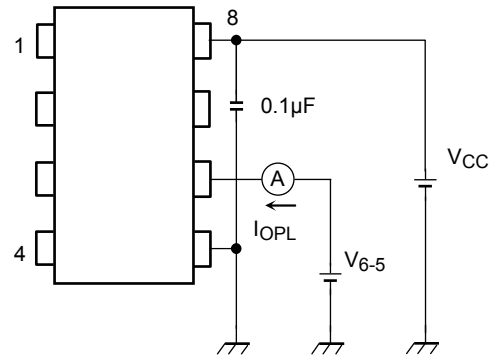
* All typical values are at Ta = 25°C

Note 7: Input signal rise time (fall time) < 0.5 μs.

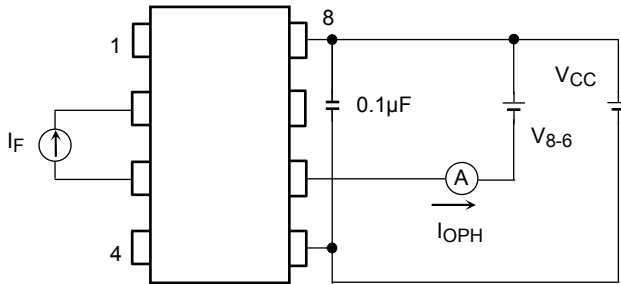
Test Circuit 1 :



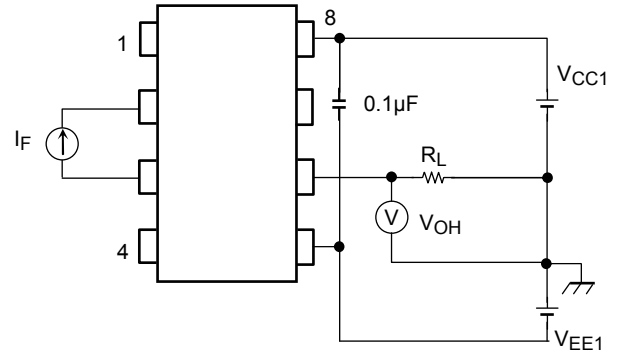
Test Circuit 2 : IOPL



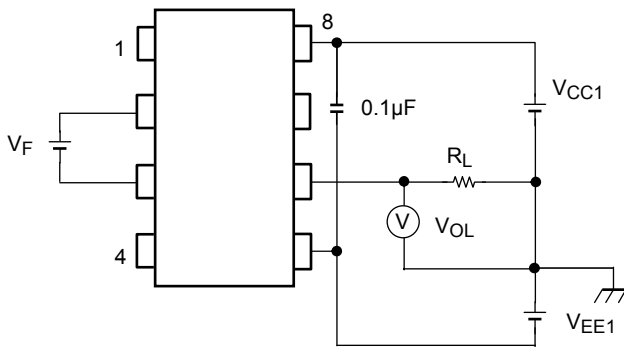
Test Circuit 3 : IOPH



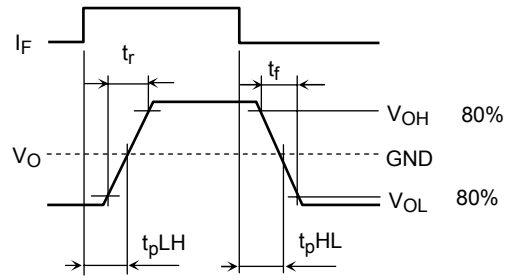
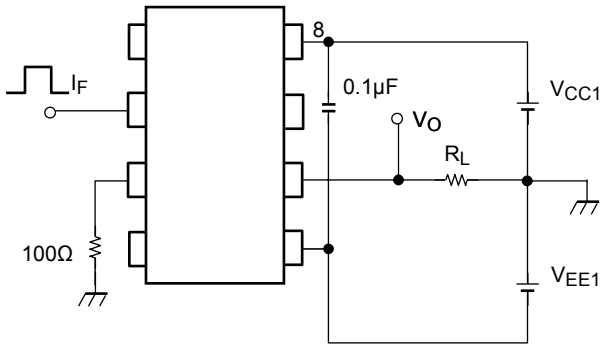
Test Circuit 4 : VOH



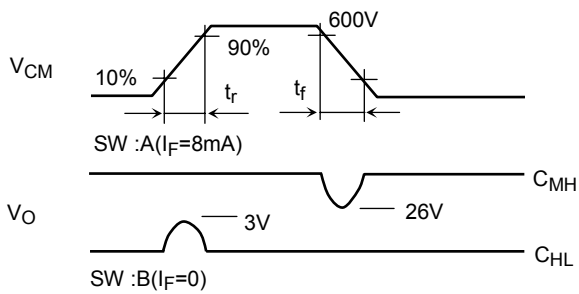
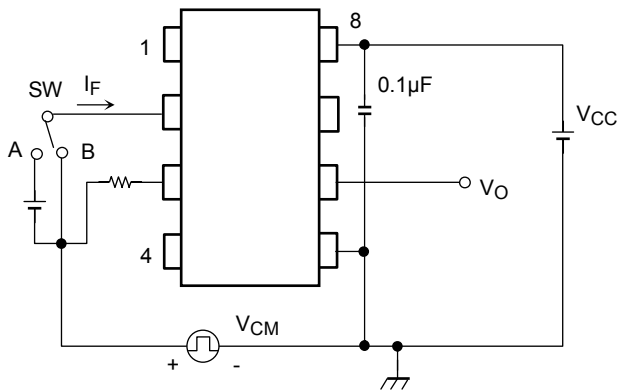
Test Circuit 5 : VOL



Test Circuit 6: t_{pLH} , t_{pHL} , t_r , t_f



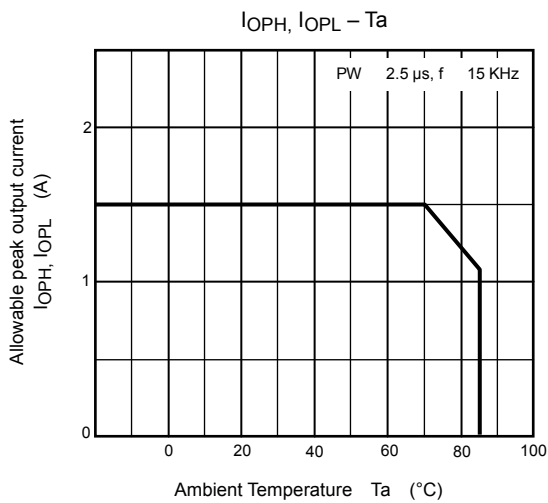
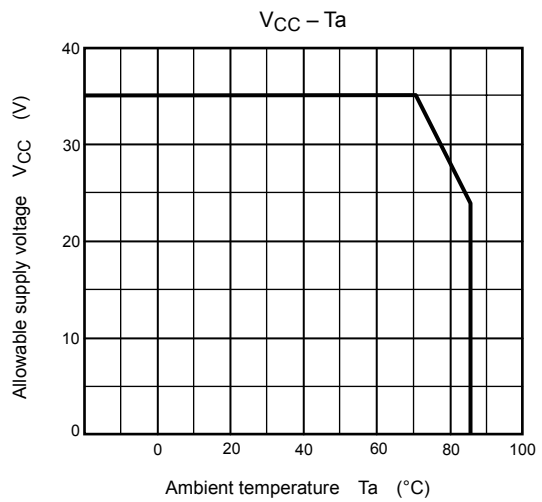
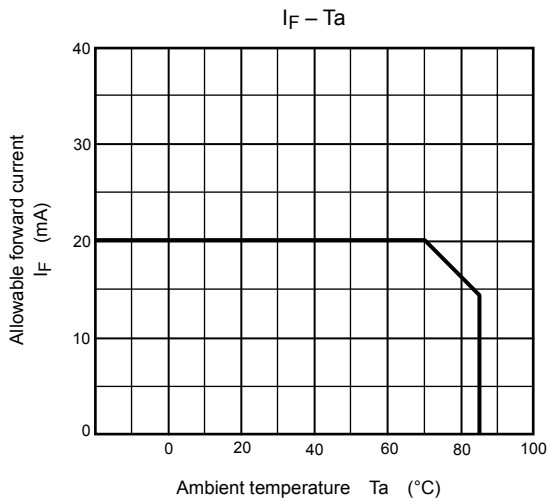
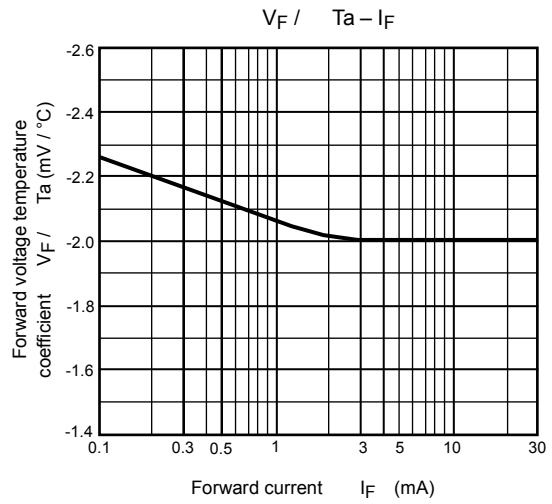
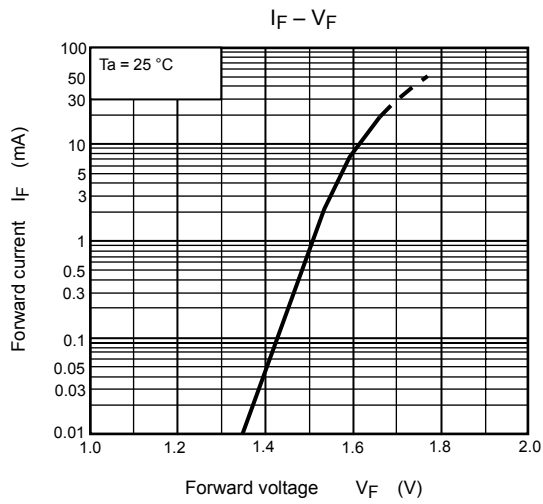
Test Circuit 7: C_{MH} , C_{ML}



$$C_{ML} = \frac{480 \text{ (V)}}{t_r \text{ (\mu s)}}$$

$$C_{MH} = \frac{480 \text{ (V)}}{t_f \text{ (\mu s)}}$$

$C_{ML}(C_{MH})$ is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.



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